UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

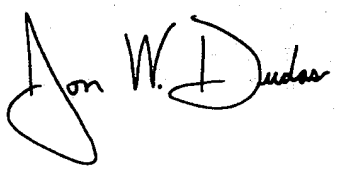
PATENT NO. : 6,967,860 B2
APPLICATION NO. : 10/683663
DATED : November 22, 2005
INVENTOR(S) : Choi et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

TITLE PAGE, ITEM (57) ABSTRACT, please replace "A ferroelectric random access memory device including a pulse generator circuit capable of generating a pulse signal in response to an address transition." with --A ferroelectric random access memory device according to the present invention includes a pulse generator circuit capable of generating a pulse signal in response to an address transition.--

Signed and Sealed this

Sixteenth Day of January, 2007



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Director of the United States Patent and Trademark Office